Model Name: DGS-1004T Ver.A1

Environmental Factor (π E): Ground Benign

λ g: Generic Failure Rate (Failure/ 10^6 hours)

π Q: Quality Factor

π L: Learning Factor

N: Quantity

λ eq: Total Failure Rate (Failure/10^6 hours)

Note 1: Referring to MIL-HDBK-217F, Notice 2, Appendix A Count Reliability Prediction,
Prediction the MTBF

Note 2: This MTBF Report doesn't include "Fan".

Note 3: Ambient : 25℃

		*	@	*	*	*	@
No.	Part Name	Part Type	λ g	π Q	π L	N	λ eq
1	Capacitor, Aluminum Oxide	187	0.0013	10		22	0.286
2	Capacitor, Ceramic(Gen. Purpose)	178	0.0017	10		4	0.068
3	Diode, Schottky barrier & Point	73	0.047	2.5		2	0.235
4	Connector, PCB card Edge	124	0.044	2		1	0.088
5	Emitter	107	0.00047	5.5		2	0.00517
6	Coil, Fixed inductor or Choke	90	0.000032	3		21	0.002016
7	Resistor, Film, Insulated	141	0.0037	10		4	0.148
8	Connector, Telephone	129	0.0082	2		4	0.0656
9	Bipolar, 1-100 Transistors	7	0.0095	10	1	3	0.285
10	Quartz Crystals	103	0.032	2.1		1	0.0672
11	Capacitor, Ceramic Chip ,CDR	181	0.0035	10		241	8.435
12	Diode, Switching	63	0.00094	5.5		2	0.01034
13	Transistors, NPN/PNP(f<200MHz)	76	0.00015	5.5		2	0.00165
14	Resistor, Film , Network	146	0.0016	10		16	0.256
15	Resistor, Film Chip	143	0.0037	10		176	6.512
16	Transformer, RF	89	0.14	3		4	1.68
17	MOS Technology, 30000-60000 Gates	19	0.13	10	1.8	1	2.34
18	MOS Technology, 1-100 Transistors	20	0.0095	10	1	7	0.665
19	MOS Technology, 3001-10000 Gates	17	0.049	10	1.7	4	3.332
20	Diode, Voltage Ref/Reg.(Avalanche & /Zer	67	0.0033	5.5		1	0.01815
21	Transistor,GaAs FET(P>=100mW)	81	0.42	5		2	4.2
22	Surface Mount Tech. Circuit Board	93	0.0025	1		1	0.0025
Total Failure Rate=							28.702626

Total Failure Rate= 28.702626 (Page 1) + 2.3459775 (Page 2-3)= 31.0486035

MTBF = 32208 Hours

Janice June 1, 2007

Janice Liu/Engineer

UP0301S-05 MTBF PREDICTION

1. METHOD : MIL - HDBK -217F (NOTICE2)

2. AMBIENT : 25 ℃

3. INPUT VOLTAGE : 115 Vac

4. OUTPUT LOAD : 5V/ 5A

5. STEADY STATE FAILURE RATE :

RESISTOR :	0.607946
CAPACITOR :	0.134667
DIODE & FET :	0.562864
OTHER :	1.040501
+)	
TOTAL :	2.3459775

6. MTBF = 1000000 / 2.3459775 = 426261.555 HRS

UP0301S-05 MTBF PREDICTION

AMBIENT : 25 ℃
I/P VOLTAGE : 115 Vac
O/P LOAD : 5 V/ 5A
DEVICE TYPE : F: FILM;MOF: METAL OXIDE FILM;CP: CHIP;TH: THERMISTOR;VR:VARIABLE

PART NO.	DEVICE TYPE	W USED	W RATED	TEMP. (℃)	STRESS	λb	πT	πP	πS	πQ	πE	λp
R15	F	0.0233	1	75.2	0.0233	0.0037	1.56698	1	0.7284325	10	1	0.042233
R16	F	0.504	1	92.6	0.504	0.0037	1.77899	1	1.2360363	10	1	0.081359
R17	F	0	0.25	52.5	0	0.0037	1.30110	0.58	0.71	10	1	0.019824
R21	F	0.0004	0.125	44.9	0.0032	0.0037	1.21534	0.44	0.7125036	10	1	0.014097
R22	F	0.0003	0.125	43.8	0.0024	0.0037	1.20307	0.44	0.7118769	10	1	0.013943
R1	F	0.0132	0.25	45.9	0.0528	0.0037	1.22652	0.58	0.7524578	10	1	0.019805
R3	MOF	0.1571	3	50.2	0.052367	0.0037	1.27495	1.5	0.7520993	10	1	0.053219
R5	MOF	0.5356	1	96.4	0.5356	0.0037	1.82608	1	1.2797563	10	1	0.086467
R6	F	0.023	1	72.7	0.023	0.0037	1.53706	1	0.7281922	10	1	0.041413
R8	F	0.0217	0.125	59.4	0.1736	0.0037	1.38046	0.44	0.8593918	10	1	0.019314
R11	F	0.0021	0.125	55.1	0.0168	0.0037	1.33084	0.44	0.7232428	10	1	0.015670
R12	F	0.0025	0.125	51.3	0.02	0.0037	1.28744	0.44	0.7257931	10	1	0.015212
R13	F	0.0021	0.125	50.6	0.0168	0.0037	1.27949	0.44	0.7232428	10	1	0.015065
R14	F	0.0006	0.125	49.8	0.0048	0.0037	1.27042	0.44	0.7137587	10	1	0.014762
R18	F	0	0.125	48.6	0	0.0037	1.25686	0.44	0.71	10	1	0.014528
R19	F	0.0012	0.125	49.6	0.0096	0.0037	1.26816	0.44	0.7175373	10	1	0.014814
R20	F	0.0004	0.125	49.3	0.0032	0.0037	1.26477	0.44	0.7125036	10	1	0.014671
R4	MOF	0.155	1	70.7	0.155	0.0037	1.51322	1	0.8419873	10	1	0.047142
R9	F	0.0052	0.125	60.2	0.0416	0.0037	1.38975	0.44	0.7432444	10	1	0.016816
R7	F	0.0054	0.125	59.1	0.0432	0.0037	1.37698	0.44	0.7445537	10	1	0.016691
VR1	VR	0.00024	0.1	43.4	0.0024	0.0037	1.57293	0.4074	0.7118769	10	1	0.016878
TH1	TH	0.182	0.459	84.2	0.396514	0.0019	1.00000	0.738	1	10	1	0.014022
SUM												0.607946